

TENTATIVE

TOSHIBA TRANSISTOR SILICON PNP EPITAXIAL TYPE

2SA1802

STROBE FLASH APPLICATIONS.
MEDIUM POWER AMPLIFIER APPLICATIONS.

- Excellent h_{FE} Linearity
: $h_{FE(1)} = 200 \sim 600$ ($V_{CE} = -2V, I_C = -0.5A$)
: $h_{FE(2)} = 140$ (Min.) ($V_{CE} = -2V, I_C = -3A$)
- Low Collector Saturation Voltage
: $V_{CE(sat)} = -0.5V$ (Max.) ($I_C = -3A, I_B = -60mA$)
- Surface Mount Package : Lead Bending Type 2-7B2A
- Complementary to 2SC4681

MAXIMUM RATINGS ($T_a = 25^\circ C$)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		V_{CBO}	-30	V
Collector-Emitter Voltage		V_{CES}	-30	V
		V_{CEO}	-10	
Emitter-Base Voltage		V_{EBO}	-6	V
Collector Current	DC	I_C	-3	A
	Pulsed (Note 1)	I_{CP}	-6	
Base Current		I_B	-0.5	A
Collector Power Dissipation	$T_a = 25^\circ C$	P_C	1.0	W
	$T_c = 25^\circ C$		10	
Junction Temperature		T_j	150	$^\circ C$
Storage Temperature Range		T_{stg}	-55~150	$^\circ C$

Note 1 : Pulse Test : Pulse Width = 10ms (Max.)
Duty Cycle = 30% (Max.)

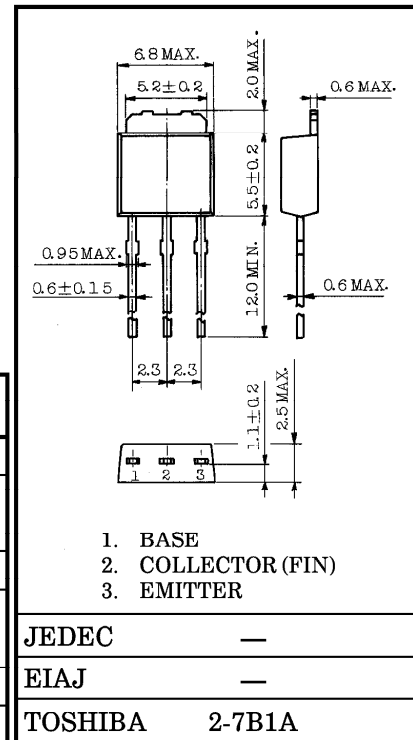
ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ C$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = -30V, I_E = 0$	—	—	-100	nA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = -6V, I_C = 0$	—	—	-100	nA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -10mA, I_B = 0$	-10	—	—	V
DC Current Gain	$h_{FE(1)}$	$V_{CE} = -2V, I_C = -0.5A$	200	—	600	
	$h_{FE(2)}$	$V_{CE} = -2V, I_C = -3A$	140	200	—	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -3A, I_B = -60mA$	—	-0.25	-0.50	V
Base-Emitter Voltage	V_{BE}	$V_{CE} = -2V, I_C = -3A$	—	-0.86	-1.2	V
Transition Frequency	f_T	$V_{CE} = -2V, I_C = -0.5A$	—	180	—	MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$	—	50	—	pF

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Unit in mm



Weight : 0.36g